## NSN 5961-00-872-8325

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-872-8325 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Overall Diameter:** 0.424 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 5.6 breakdown voltage, dc **Voltage Tolerance In Percent:** -5.0/+5.0 **Current Rating Per Characteristic:** 445.00 milliamperes all primaries horsepower metric and 1.68 amperes source cutoff current horsepower metric **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius case **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Specification Data:** 81349-mil-s-19500/272 government specification Shelf Life: N/a

No

**Unit Of Measure:** 

**Demilitarization:** 

## NSN 5961-00-872-8325

Diode Semiconductor Device - Page 2 of 2



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